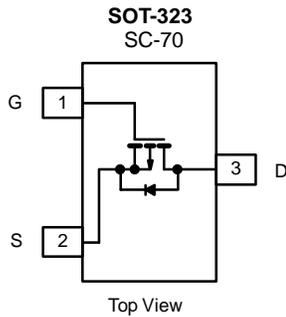


SSF84W-VB Datasheet

P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	V _{GS(th)} (V)	I _D (mA)
- 60	4 at V _{GS} = - 10 V	- 1 to - 3	- 135



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- High-Side Switching
- Low On-Resistance: 4 Ω
- Low Threshold: - 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Power Supply Converter Circuits
- Solid-State Relays

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Easily Driven without Buffer

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 60	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current ^a	I _D	T _A = 25 °C	- 135
		T _A = 100 °C	- 105
Pulsed Drain Current ^b	I _{DM}	- 800	mA
Power Dissipation ^a	P _D	T _A = 25 °C	350
		T _A = 100 °C	140
Maximum Junction-to-Ambient ^a	R _{thJA}	350	°C/W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

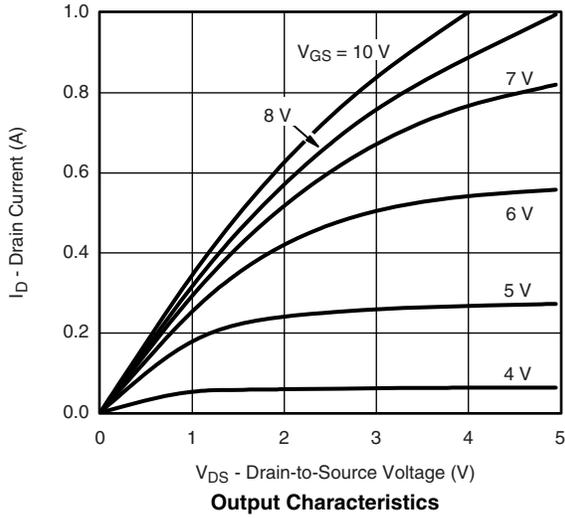
SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ. ^a	Max.	
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$	- 60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 10	μA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			± 200	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}, T_J = 85\text{ }^\circ\text{C}$			± 500	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$			- 25	
		$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			- 250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = -4.5\text{ V}$	- 50			mA
		$V_{GS} = -10\text{ V}, V_{DS} = -10\text{ V}$	- 600			
Drain-Source On-Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -25\text{ mA}$		5		Ω
		$V_{GS} = -10\text{ V}, I_D = -100\text{ mA}$		4		
		$V_{GS} = -10\text{ V}, I_D = -100\text{ mA}, T_J = 125\text{ }^\circ\text{C}$			9	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -100\text{ mA}$	80			mS
Diode Forward Voltage	V_{SD}	$I_S = -100\text{ mA}, V_{GS} = 0\text{ V}$			- 1.4	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = -30\text{ V}, V_{GS} = -15\text{ V}$ $I_D \cong -100\text{ mA}$		1.7		nC
Gate-Source Charge	Q_{gs}			0.26		
Gate-Drain Charge	Q_{gd}			0.46		
Input Capacitance	C_{iss}	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$		23		pF
Output Capacitance	C_{oss}			10		
Reverse Transfer Capacitance	C_{rss}			5		
Switching^b						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -25\text{ V}, R_L = 150\text{ }\Omega$ $I_D \cong -200\text{ mA}, V_{GEN} = -10\text{ V}, R_g = 10\text{ }\Omega$		20		ns
Turn-Off Time	$t_{d(off)}$			35		

Notes:

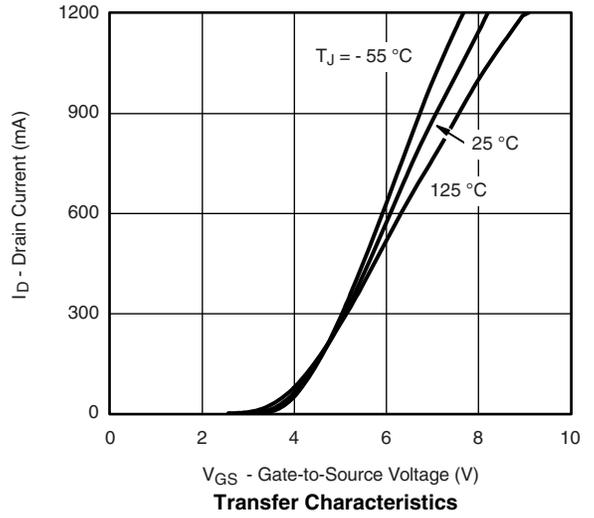
- a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
 b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

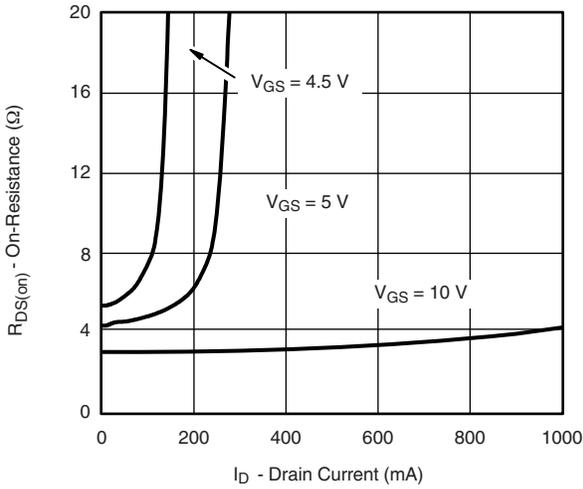
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



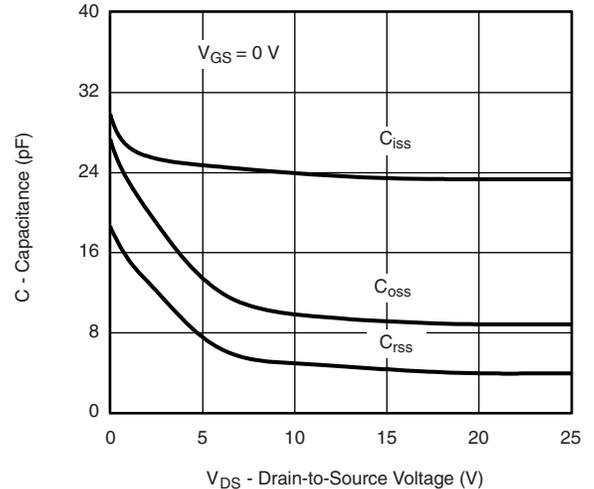
Output Characteristics



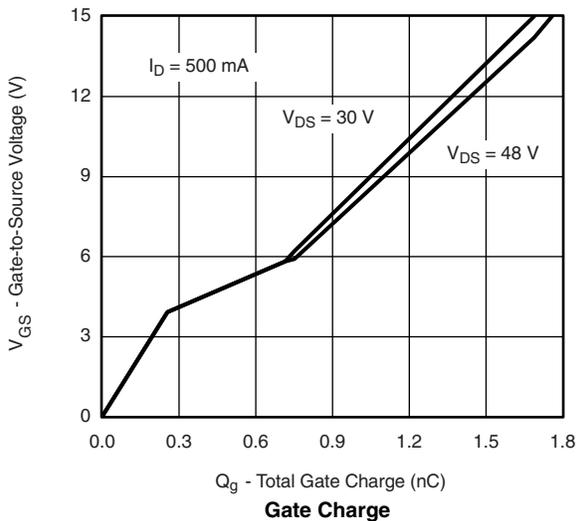
Transfer Characteristics



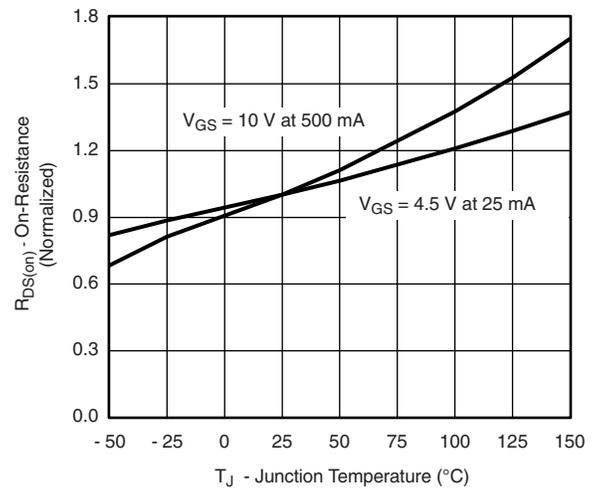
On-Resistance vs. Drain Current



Capacitance

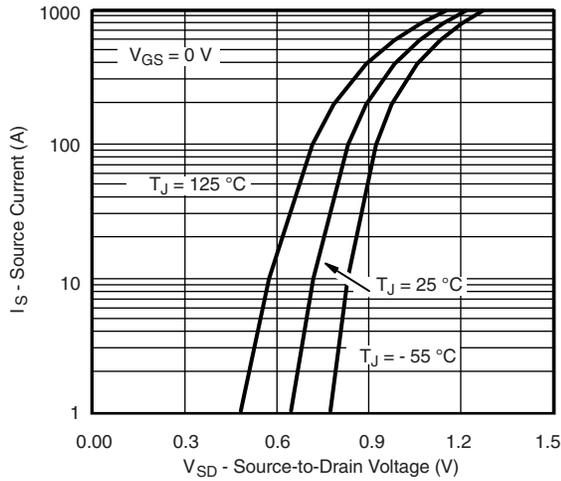


Gate Charge

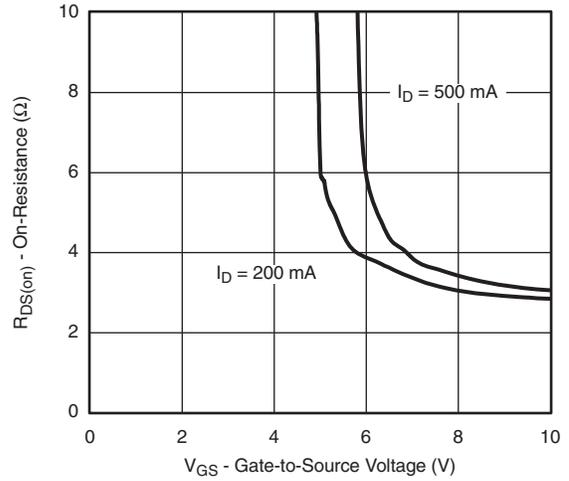


On-Resistance vs. Junction Temperature

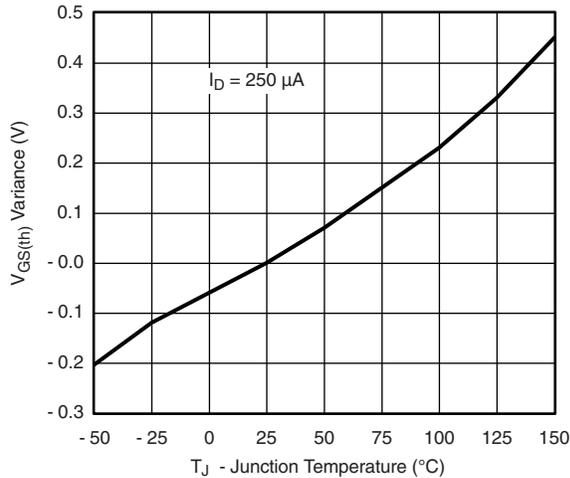
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



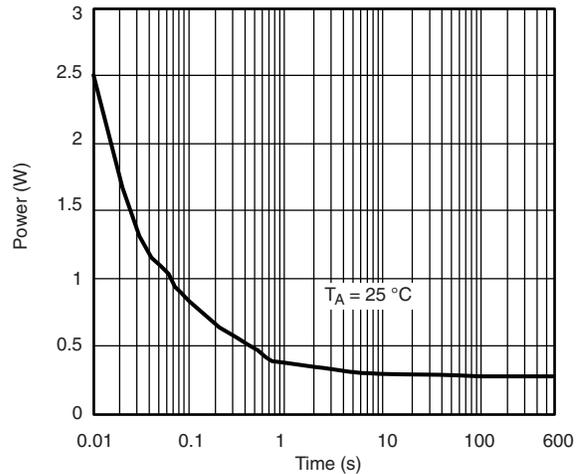
Source-Drain Diode Forward Voltage



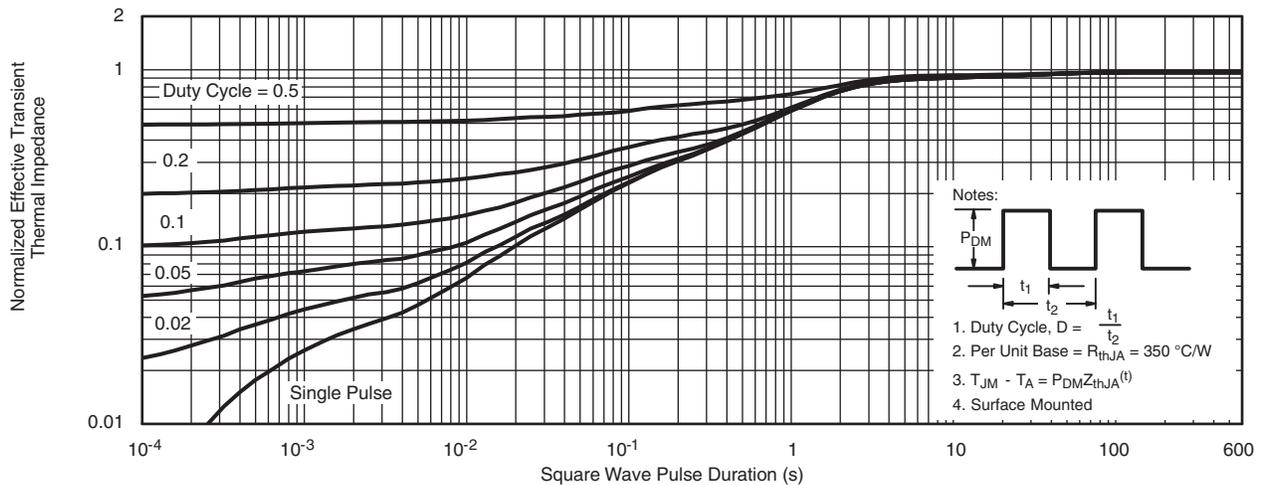
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature

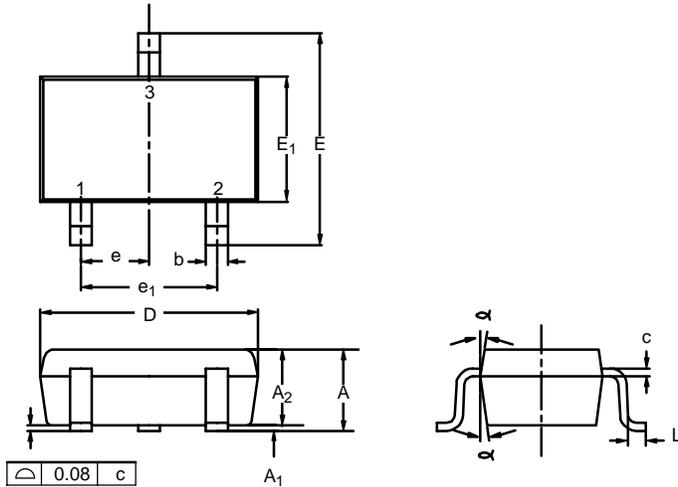


Single Pulse Power, Junction-to-Ambient



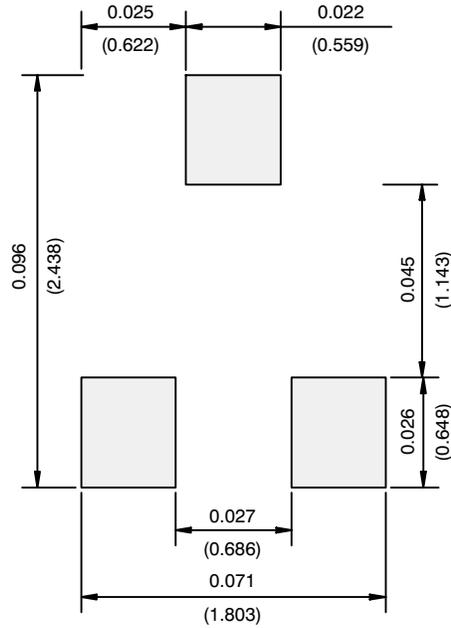
Normalized Thermal Transient Impedance, Junction-to-Ambient

SC-70: 3-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	-	1.10	0.035	-	0.043
A₁	-	-	0.10	-	-	0.004
A₂	0.80	-	1.00	0.031	-	0.039
b	0.25	-	0.40	0.010	-	0.016
c	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		
ECN: S-03946—Rev. C, 09-Jul-01 DWG: 5549						

RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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